

What is claimed is:

1. A pattern forming method for forming a resist pattern on a substrate having a plurality of divided exposure regions, the resist pattern extending across a first divided exposure region and a second divided exposure region among the plurality of divided exposure regions, the method comprising the steps of:

forming a resist film on the substrate;

exposing the resist film in the first divided exposure region to form a latent image which defines one edge of the resist pattern in the vicinity of a boundary between the first divided exposure region and the second divided exposure region;

exposing the resist film in the second divided exposure region to form a latent image which defines another edge of the resist pattern in the vicinity of the boundary or one edge of another resist pattern located opposite to that edge; and

developing the resist film to form the resist pattern.

2. A pattern forming method for forming a wiring pattern on a substrate having a plurality of divided exposure regions, the wiring pattern extending across a first divided exposure region and a second divided exposure region adjacent to each other among the plurality of divided exposure regions, the method comprising the steps of:

forming a wiring layer for forming the wiring pattern on the substrate;

forming a resist film on the wiring layer;

exposing the resist film in the first divided exposure region using a first exposure mask to form a latent image which defines one edge of the wiring pattern in the vicinity of a boundary between the first divided exposure region and the second divided exposure region;

exposing the resist film in the second divided exposure region using a second exposure mask to form a latent image which defines another edge of the wiring pattern in the vicinity of the boundary;

developing the resist film to form the resist pattern;

etching the wiring layer using the resist pattern as an etching mask to form the wiring pattern; and

correcting a relative misalignment of the first and second exposure masks relative to the substrate based on a pattern width of the wiring pattern formed in the vicinity of the boundary.

3. A pattern forming method according to claim 2, wherein the correction is made by measuring the pattern width of the wiring pattern and calculating the direction and amount of a misalignment of the first and second exposure masks relative to the substrate.

4. A method of manufacturing a thin film transistor substrate, comprising the steps of forming a plurality of bus lines extending on a substrate with an insulation film interposed; and forming a plurality of thin film transistors connected to any of the plurality of bus lines, wherein the bus lines are formed using the pattern forming method according to

claim 1.

5. A method of manufacturing a thin film transistor substrate, comprising the steps of forming a plurality of bus lines extending on a substrate with an insulation film interposed; and forming a plurality of thin film transistors connected to any of the plurality of bus lines, wherein the bus lines are formed using the pattern forming method according to claim 2.

6. A method of manufacturing a thin film transistor substrate, comprising the steps of forming a plurality of bus lines extending on a substrate with an insulation film interposed; and forming a plurality of thin film transistors connected to any of the plurality of bus lines, wherein the bus lines are formed using the pattern forming method according to claim 3.

7. A method of manufacturing a thin film transistor substrate according to claim 4, wherein the bus lines are storage capacitor bus lines.

8. A method of manufacturing a thin film transistor substrate according to claim 5, wherein the bus lines are storage capacitor bus lines.

9. A method of manufacturing a thin film transistor substrate according to claim 6, wherein the bus lines are storage

capacitor bus lines.

10. A method of manufacturing a liquid crystal display comprising a liquid crystal sealed between two substrates, wherein at least either of the two substrates is fabricated using the method of manufacturing a thin film transistor substrate according to claim 4.

11. A method of manufacturing a liquid crystal display comprising a liquid crystal sealed between two substrates, wherein at least either of the two substrates is fabricated using the method of manufacturing a thin film transistor substrate according to claim 5.

12. A method of manufacturing a liquid crystal display comprising a liquid crystal sealed between two substrates, wherein at least either of the two substrates is fabricated using the method of manufacturing a thin film transistor substrate according to claim 6.

13. A method of manufacturing a liquid crystal display comprising a liquid crystal sealed between two substrates, wherein at least either of the two substrates is fabricated using the method of manufacturing a thin film transistor substrate according to claim 7.

14. A method of manufacturing a liquid crystal display comprising a liquid crystal sealed between two substrates,

wherein at least either of the two substrates is fabricated using the method of manufacturing a thin film transistor substrate according to claim 8.

15. A method of manufacturing a liquid crystal display comprising a liquid crystal sealed between two substrates, wherein at least either of the two substrates is fabricated using the method of manufacturing a thin film transistor substrate according to claim 9.

16. An exposure mask having writing patterns which are provided in a plurality of divided exposure regions and which form a resist pattern extending across the plurality of divided exposure regions when stitched together and a shielding band for shielding the neighborhood of a boundary between the divided exposure regions from light, the mask comprising:

a cutout provided by cutting the shielding band such that it defines one edge of the resist pattern in the vicinity of the boundary; and

a protrusion protruding from the shielding band such that a part of another edge of the resist pattern in the vicinity of the boundary is not defined.

17. A pair of exposure masks each having writing patterns which are provided in a plurality of divided exposure regions and which form a resist pattern extending across the plurality of divided exposure regions when stitched together and a shielding band for shielding the neighborhood of a boundary

between the divided exposure regions from light, comprising:

a first exposure mask having a cutout provided by cutting the shielding band such that it defines one edge of the resist pattern in the vicinity of the boundary and a protrusion protruding from the shielding band such that a part of another edge of the resist pattern in the vicinity of the boundary is not defined; and

a second exposure mask having a cutout provided by cutting the shielding band such that it defines the other edge of the resist pattern in the vicinity of the boundary and a protrusion protruding from the shielding band such that a part of the one edge of the resist pattern in the vicinity of the boundary is not defined.